

MA3D760

Silicon epitaxial planar type (cathode common)

For switching power supply

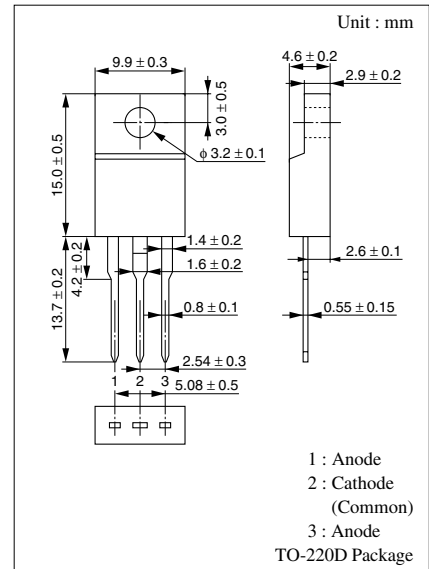
■ Features

- Low forward rise voltage V_F
- TO-220D (Full-pack package) with high dielectric breakdown voltage > 5.0 kV
- Easy-to-mount, caused by its V cut lead end

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Rating | Unit |
|--|-------------|-------------|------------------|
| Repetitive peak reverse voltage | V_{RRM} | 90 | V |
| Average forward current | $I_{F(AV)}$ | 5 | A |
| Non-repetitive peak forward surge current* | I_{FSM} | 80 | A |
| Junction temperature | T_j | -40 to +125 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -40 to +125 | $^\circ\text{C}$ |

Note) * : Half sine-wave; 10 ms/cycle



■ Electrical Characteristics $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|----------------------|---------------|--|-----|-----|------|--------------------|
| Reverse current (DC) | I_R | $V_R = 90$ V, $T_C = 25^\circ\text{C}$ | | | 1 | mA |
| Forward voltage (DC) | V_F | $I_F = 2.5$ A, $T_C = 25^\circ\text{C}$ | | | 0.80 | V |
| Thermal resistance* | $R_{th(j-c)}$ | Direct current (between junction and case) | | | 3 | $^\circ\text{C/W}$ |

Note) 1. Rated input/output frequency: 200 MHz

2. * : $T_C = 25^\circ\text{C}$

